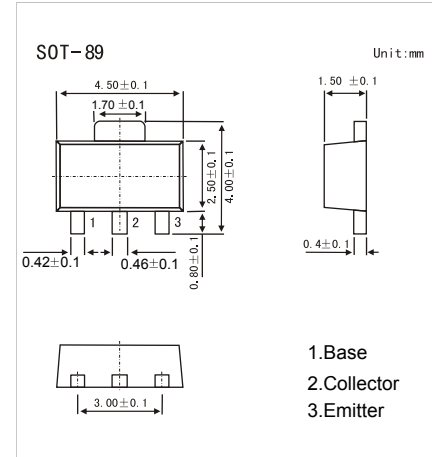


**PNP Transistors**

**2SB1260**

■ Features

- High breakdown voltage and high current.
- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Good  $h_{FE}$  linearity.
- Complementary to 2SD1898



■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	-80	V
Collector - Emitter Voltage	$V_{CE0}$	-80	
Emitter - Base Voltage	$V_{EB0}$	-5	
Collector Current - Continuous	$I_C$	-1	A
Collector current -Pulse	$I_{CP}$	-2	
Collector Power Dissipation	$P_C$	0.5	W
		2	
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CB0}$	$I_C = -100 \mu\text{A}, I_E = 0$	-80			V
Collector- emitter breakdown voltage	$V_{CE0}$	$I_C = -1 \text{ mA}, I_B = 0$	-80			
Emitter - base breakdown voltage	$V_{EB0}$	$I_E = -100 \mu\text{A}, I_C = 0$	-5			
Collector-base cut-off current	$I_{CB0}$	$V_{CB} = -60\text{V}, I_E = 0$			-1	$\mu\text{A}$
Emitter cut-off current	$I_{EB0}$	$V_{EB} = -4\text{V}, I_C = 0$			-1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$			-0.4	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$			-1.2	
DC current gain	$h_{FE}$	$V_{CE} = -3\text{V}, I_C = -100 \text{ mA}$	120		390	
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		20		pF
Transition frequency	$f_T$	$V_{CE} = -10\text{V}, I_E = 50 \text{ mA}, f = 100\text{MHz}$		100		MHz

■ Classification of  $h_{fe}$

Type	2SB1260-Q	2SB1260-R
Range	120-270	180-390
Marking	BE Q*	BE R*

## PNP Transistors

### 2SB1260

#### ■ Typical Characteristics

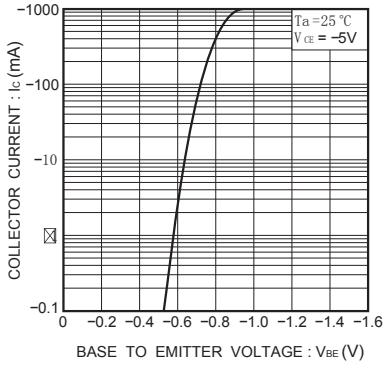


Fig.1 Grounded emitter propagation characteristics

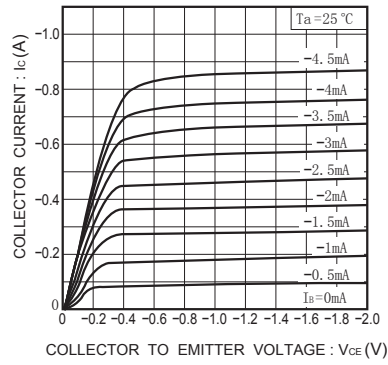


Fig.2 Grounded emitter output characteristics

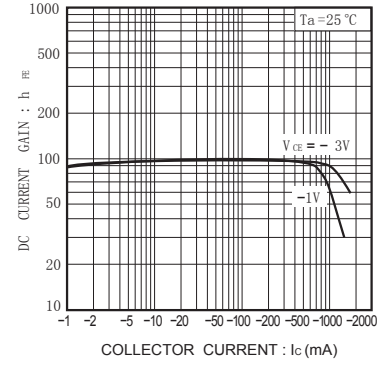


Fig.3 DC current gain vs. collector current

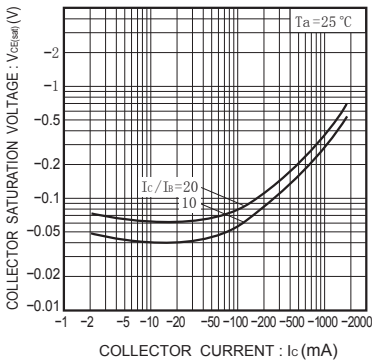


Fig.4 Collector-emitter saturation voltage vs. collector current

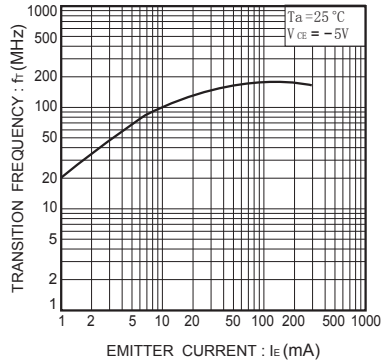


Fig.5 Gain bandwidth product vs. emitter current

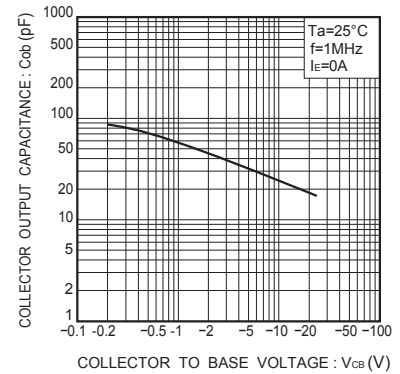


Fig.6 Collector output capacitance vs. collector-base voltage